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| APPLICATION NO. | FILING DATE | FIRST NAMED INVENTOR | ATTORNEY DOCKET NO. | CONFIRMATION NO. |
|---|-----------------------------------|------------------------|-----------------------------|------------------|
| 10/764,938 | 01/26/2004 | Mohammed A. Fathimulla | P02,0004 01 H0002270 DIV | 9312 |
| | 7590 05/15/200 INTERNATIONAL I | EXAMINER | | |
| 101 COLUMBI | | PHAM, LONG | | |
| P O BOX 2245 MORRISTOWN, NJ 07962-2245 | | | ART UNIT | PAPER NUMBER |
| | , | | 2814 | |
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| | | | 05/15/2007 | PAPER |

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

| | Application No. | Applicant(s) | | | | |
|--|--|---|--|--|--|--|
| | 10/764,938 | FATHIMULLA ET AL. | | | | |
| Office Action Summary | Examiner | Art Unit | | | | |
| | Long Pham | 2814 | | | | |
| The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply | | | | | | |
| A SHORTENED STATUTORY PERIOD FOR REPLY WHICHEVER IS LONGER, FROM THE MAILING DA - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. If NO period for reply is specified above, the maximum statutory period was reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b). | ATE OF THIS COMMUNI 36(a). In no event, however, may a vill apply and will expire SIX (6) MO , cause the application to become A | CATION. reply be timely filed NTHS from the mailing date of this communication. BANDONED (35 U.S.C. § 133). | | | | |
| Status | | | | | | |
| 1) Responsive to communication(s) filed on 15 Fe | Responsive to communication(s) filed on <u>15 February 2007</u> . | | | | | |
| | This action is FINAL . 2b) This action is non-final. | | | | | |
| , | Since this application is in condition for allowance except for formal matters, prosecution as to the merits is | | | | | |
| closed in accordance with the practice under E | x parte Quayle, 1935 C.I |). 11, 453 O.G. 213. | | | | |
| Disposition of Claims | | | | | | |
| 4) Claim(s) 1-6 and 22-35 is/are pending in the ap 4a) Of the above claim(s) 22-31 is/are withdraw 5) Claim(s) is/are allowed. 6) Claim(s) 1-6 and 32-35 is/are rejected. 7) Claim(s) is/are objected to. 8) Claim(s) are subject to restriction and/or | vn from consideration. | | | | | |
| Application Papers | | | | | | |
| 9) The specification is objected to by the Examine 10) The drawing(s) filed on is/are: a) acce Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) The oath or declaration is objected to by the Ex | epted or b) objected to drawing(s) be held in abeya ion is required if the drawing | nce. See 37 CFR 1.85(a). g(s) is objected to. See 37 CFR 1.121(d). | | | | |
| Priority under 35 U.S.C. § 119 | | | | | | |
| 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No. 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. | | | | | | |
| Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO/SB/08) Paper No(s)/Mail Date 04/12/07. | Paper No | Summary (PTO-413) s)/Mail Date informal Patent Application | | | | |

Art Unit: 2814

DETAILED ACTION

New grounds of rejection

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claim 1 is rejected under 35 U.S.C. 102(b) as being anticipated by Nakagawa et al. (US pat 5,438,220).

With respect to claim 1, Nakagawa et al. teach a semiconductor device comprising (see fig. 18 and associated text):

A high resistivity polysilicon handle wafer or polycrystalline layer 234;

A buried oxide layer 2 located directly on a single surface of the polysilicon handle wafer; and

A silicon layer 4 located directly on the buried oxide layer.

Claims 3 and 4 are rejected under 35 U.S.C. 102(b) as being anticipated by Nakagawa et al. (US pat 5,438,220).

With respect to claim 1, Nakagawa et al. teach a semiconductor device comprising (see fig. 18 and associated text):

A high resistivity polysilicon handle wafer or polycrystalline layer 234;

A buried oxide layer 2 located directly on a single surface of the polysilicon handle wafer or polycrystalline layer; and

A silicon layer 4 located directly on the buried oxide layer.

Claim Rejections - 35 USC § 103

Art Unit: 2814

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 2, 32, and 33 are rejected under 35 U.S.C. 103(a) as being unpatentable over Nakagawa et al. (US pat 5,438,220) as applied to claim 1 above, and further in view of the a pplicant's admitted prior art (AAPA) of this application and Temple et al. (US pat 4,905,075).

With respec to claim 2, Nakagawa et al. teach the wafer having high resistivity or updoped polysilicon but fail to teach that the device has an RF input.

AAPA teaches using high resistivity substrate or wafer to form RF device. See the Background of the Invention on pages 1 and 2 of this application.

It would have been obvious to one of <u>ordinary skill</u> in the art of making semiconductor devices to include an RF input on the wafer of Nakagawa et al. to form an RF device having reduced losses and cross-talk. See the background of the Invention on pages 1 and 2 of this application.

With respect claim 32, Nakagawa et al. in combination with AAPA fail to teach that the polysilicon handle wafer has a resistivity of greater than 10⁶ ohm-cm.

Temple et al. teach using a polysilicon wafer or handle having a resistivity of greater than 10⁶ ohm-cm to provide a structure that can withstand mechanical shock. See col. 2, lines 1-5 and col. 5, lines 20-35.

Application/Control Number: 10/764,938

Art Unit: 2814

It would have been obvious to one of <u>ordinary skill</u> in the art of making semiconductor devices to incorporate the teaching of Temple et al. into the structure of Annamalai and AAPA to achieve the above benefit.

With respect to claim 33, AAPA further teaches forming RF component in the silicon layer or wafer to reduce cross-talk.

Claims 5, 6, 34, and 35 are rejected under 35 U.S.C. 103(a) as being unpatentable over Nakagawa et al. (US pat 5,438,220) as applied to claims 3 and 4 above, and further in view of the a pplicant's admitted prior art (AAPA) of this application and Temple et al. (US pat 4,905,075).

With respec to claim 5, Nakagawa et al. teach the wafer having high resistivity or updoped polysilicon but fail to teach that the device has an RF input.

AAPA teaches using high resistivity substrate or wafer to form RF device. See the Background of the Invention on pages 1 and 2 of this application.

It would have been obvious to one of <u>ordinary skill</u> in the art of making semiconductor devices to include an RF input on the wafer of Nakagawa et al. to form an RF device having reduced losses and cross-talk. See the background of the Invention on pages 1 and 2 of this application.

With respect to claim 6, Nakagawa et al. further teach the wafer is made of polysilicon or polycrystalline.

With respect claim 34, Nakagawa et al. in combination with AAPA fail to teach that the polysilicon handle wafer has a resistivity of greater than 10⁶ ohmom.

Temple et al. teach using a polysilicon wafer or handle having a resistivity of greater than 10⁶ ohm-cm to provide a structure that can withstand mechanical shock. See col. 2, lines 1-5 and col. 5, lines 20-35.

Art Unit: 2814

It would have been obvious to one of <u>ordinary skill</u> in the art of making semiconductor devices to incorporate the teaching of Temple et al. into the structure of Annamalai and AAPA to achieve the above benefit.

With respect to claim 35, AAPA further teaches forming RF component in the silicon layer or wafer to reduce cross-talk.

Response to Arguments

Applicant's arguments with respect to claims 1-6 and 32-35 have been considered but are most in view of the new ground(s) of rejection.

Conclusion

Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Long Pham whose telephone number is 571-272-1714. The examiner can normally be reached on Mon-Frid, 10am to 5pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael Fahmy can be reached on 571-272-1705. The fax

Application/Control Number: 10/764,938 Page 6

Art Unit: 2814

phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

Long Pham
Primary Examiner
Art Unit 2814